	Hits	Search Text	DBs
1	301	((metal$4 or film or dielectric or ((under or bottom) near8 (layer or film or coat$3))) same (photoresist or resist or photo$4cur$4 or photo$3imageable) same (novolac or epoxy or resin) same (((photoactive or photo$4acid) near7 (generat$4 or liberat$4)) or PAG or (acid near8 (generat$4 or liberat$4))) same (expos$4 or illuminat$4 or irradiat$4)) and develop$4 and ((solubilization or solubilizing or soluble or solubility or insoluble) same (prevent$4 or caus$4 or inhibit$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
2	120	((metal$4 or film or dielectric or ((under or bottom) near8 (layer or film or coat$3))) same (photoresist or resist or photo$4cur$4 or photo$3imageable) same (novolac or epoxy or resin) same (((photoactive or photo$4acid) near7 (generat$4 or liberat$4)) or PAG or (acid near8 (generat$4 or liberat$4))) same (expos$4 or illuminat$4 or irradiat$4)) and develop$4 and ((solubilization or solubilizing or soluble or solubility or insoluble) same (prevent$4 or caus$4 or inhibit$4)) and polyhydroxystyrene	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
3	1	((metal$4 or film or dielectric or ((under or bottom) near8 (layer or film or coat$3))) same (photoresist or resist or photo$4cur$4 or photo$3imageable) same (novolac or epoxy or resin) same (((photoactive or photo$4acid) near7 (generat$4 or liberat$4)) or PAG or (acid near8 (generat$4 or liberat$4))) same (expos$4 or illuminat$4 or irradiat$4) same ((upper or top) near9 (layer or coat$4 or film))) and develop$4 and ((solubilization or solubilizing or soluble or solubility or insoluble) same (prevent$4 or caus$4 or inhibit$4)) and polyhydroxystyrene	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
4	182	430/270.1.ccls. and ((metal$4 or film or dielectric or ((under or bottom) near8 (layer or film or coat$3))) same (photoresist or resist or photo$4cur$4 or photo$3imageable) same (novolac or epoxy or resin) same (((photoactive or photo$4acid) near7 (generat$4 or liberat$4)) or PAG or (acid near8 (generat$4 or liberat$4))) same (expos$4 or illuminat$4 or irradiat$4)) and develop$4 and ((solubilization or solubilizing or soluble or solubility or insoluble) same (prevent$4 or caus$4 or inhibit$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
5	2	((metal$4 or dielectric or ((under or bottom or conductive) near14 (layer or film or coat$3))) same (photoresist or resist or photo$4cur$4 or photo$3imageable) same (novolac or epoxy or resin) same (((photoactive or photo$4acid) near7 (generat$4 or liberat$4)) or PAG or (acid near8 (generat$4 or liberat$4))) same (expos$4 or illuminat$4 or irradiat$4) same ((upper or top or outer or protective or mask or pattern$3) near9 (layer or coat$4 or film))) and develop$4 and (solubilization or $3solubilizing or soluble or solubility or insoluble) and polyhydroxystyrene	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
6	128	((under or bottom or conductive or metal$4 or dielectric) near14 (deposit$4 or form$3 or layer or film or coat$3)) and ((photoresist or resist or photo$4cur$4 or photo$3imageable) same (novolac or epoxy or resin$3) same (((photoactive or photo$4acid) near7 (generat$4 or liberat$4)) or PAG or (acid near8 (generat$4 or liberat$4))) same (expos$4 or illuminat$4 or irradiat$4) same pattern$4) and develop$4 and ((solubilization or $3solubilizing or soluble or solubility or insoluble) same (prevent$4 or caus$4 or inhibit$4)) and polyhydroxystyrene	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
7	0	((under or bottom or conductive or metal$4 or dielectric) near14 (deposit$4 or form$3 or layer or film or coat$3)) and ((photoresist or resist or photo$4cur$4 or photo$3imageable) same (novolac or epoxy or resin$3) same (((photoactive or photo$4acid) near7 (generat$4 or liberat$4)) or PAG or (acid near8 (generat$4 or liberat$4))) same (expos$4 or illuminat$4 or irradiat$4) same pattern$4) and develop$4 and ((solubilization or $3solubilizing or soluble or solubility or insoluble) same (prevent$4 or caus$4 or inhibit$4)) and polyhydroxystyrene and ((CD or (critical near5 dimension)) same etch$4 same (feature or lines or contact) same (LER or LWR or (line near4 (wid$2 or edge) near4 rough$5)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
8	0	((under or bottom or conductive or metal$4 or dielectric) near14 (deposit$4 or form$3 or layer or film or coat$3)) and ((photoresist or resist or photo$4cur$4 or photo$3imageable) same (novolac or epoxy or resin$3) same (((photoactive or photo$4acid) near7 (generat$4 or liberat$4)) or PAG or (acid near8 (generat$4 or liberat$4))) same (expos$4 or illuminat$4 or irradiat$4) same pattern$4) and develop$4 and ((solubilization or $3solubilizing or soluble or solubility or insoluble) same (prevent$4 or caus$4 or inhibit$4)) and polyhydroxystyrene and ((CD or (critical near5 dimension)) same (feature or lines or contact) same (LER or LWR or (line near4 (wid$2 or edge) near4 rough$5))) and (etch$4 or RIE or (dry near5 etch$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
9	3	((under or bottom or conductive or metal$4 or dielectric) near14 (deposit$4 or form$3 or layer or film or coat$3)) and ((photoresist or resist or photo$4cur$4 or photo$3imageable) same (novolac or epoxy or resin$3) same (((photoactive or photo$4acid) near7 (generat$4 or liberat$4)) or PAG or (acid near8 (generat$4 or liberat$4))) same (expos$4 or illuminat$4 or irradiat$4) same pattern$4) and develop$4 and ((solubilization or $3solubilizing or soluble or solubility or insoluble) same (prevent$4 or caus$4 or inhibit$4)) and polyhydroxystyrene and ((CD or (critical near5 dimension)) same (feature or lines or contact)) and (LER or LWR or (line near4 (wid$2 or edge) near4 rough$5)) and (etch$4 or RIE or (dry near5 etch$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
10	0	(((under or bottom or conductive or metal$4 or dielectric) near14 (deposit$4 or form$3 or layer or film or coat$3)) same pattern$4) and ((photoresist or resist or photo$4cur$4 or photo$3imageable) same (novolac or epoxy or resin$3) same (((photoactive or photo$4acid) near7 (generat$4 or liberat$4)) or PAG or (acid near8 (generat$4 or liberat$4))) same (expos$4 or illuminat$4 or irradiat$4) same pattern$4) and develop$4 and ((solubilization or $3solubilizing or soluble or solubility or insoluble) same (prevent$4 or caus$4 or inhibit$4)) and polyhydroxystyrene and (CD or (critical near5 dimension)) and (LER or LWR or (line near4 (wid$2 or edge) near4 rough$5)) and (etch$4 or RIE or (dry near5 etch$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
11	8	((under or bottom or conductive or metal$4 or dielectric) near14 (deposit$4 or form$3 or layer or film or coat$3)) and ((photoresist or resist or photo$4cur$4 or photo$3imageable) same (novolac or epoxy or resin$3) same (vinyl near9 phen$3) same (((photoactive or photo$4acid) near7 (generat$4 or liberat$4)) or PAG or (acid near8 (generat$4 or liberat$4))) same (expos$4 or illuminat$4 or irradiat$4) same pattern$4) and develop$4 and ((solubilization or $3solubilizing or soluble or solubility or insoluble) same (prevent$4 or caus$4 or inhibit$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
12	194	(((under or bottom or conductive or metal$4 or dielectric) near14 (deposit$4 or form$3 or layer or film or coat$3)) same pattern$4) and ((photoresist or resist or photo$4cur$4 or photo$3imageable) same (novolac or epoxy or resin$3) same (((photoactive or photo$4acid) near7 (generat$4 or liberat$4)) or PAG or (acid near8 (generat$4 or liberat$4))) same (expos$4 or illuminat$4 or irradiat$4) same pattern$4) and develop$4 and ((solubilization or $3solubilizing or soluble or solubility or insoluble) same (prevent$4 or caus$4 or inhibit$4)) and (etch$4 or RIE or (dry near5 etch$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
13	24	(((under or bottom or conductive or metal$4 or dielectric) near14 (deposit$4 or form$3 or layer or film or coat$3)) same pattern$4) and ((photoresist or resist or photo$4cur$4 or photo$3imageable) same (novolac or epoxy or resin$3) same (((photoactive or photo$4acid) near7 (generat$4 or liberat$4)) or PAG or (acid near8 (generat$4 or liberat$4))) same (expos$4 or illuminat$4 or irradiat$4) same pattern$4) and develop$4 and ((solubilization or $3solubilizing or soluble or solubility or insoluble) same (prevent$4 or caus$4 or inhibit$4)) and (etch$4 or RIE or (dry near5 etch$4)) and (vinyl near9 phenol) and $4hydroxy$3styrene	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
14	11	(((under or bottom or conductive or metal$4 or dielectric) near14 (deposit$4 or form$3 or layer or film or coat$3)) same pattern$4) and ((photoresist or resist or photo$4cur$4 or photo$3imageable) same (((photoactive or photo$4acid) near7 (generat$4 or liberat$4)) or PAG or (acid near8 (generat$4 or liberat$4))) same (expos$4 or illuminat$4 or irradiat$4) same pattern$4) and develop$4 and (etch$4 or RIE or (dry near5 etch$4)) and ((CD or (critical near5 dimension)) same (feature or line or contact)) and (LER or LWR or (line near4 (wid$2 or edge) near4 rough$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
15	23	(((under or bottom or conductive or metal$4 or dielectric) near14 (deposit$4 or form$3 or layer or film or coat$3)) same pattern$4) and ((photoresist or resist or photo$4cur$4 or photo$3imageable) same (expos$4 or illuminat$4 or irradiat$4) same (EUV or (KrF near5 (light or laser)) or excimer) same pattern$4) and develop$4 and (etch$4 or RIE or (dry near5 etch$4)) and (CD or (critical near5 dimension)) and (LER or LWR or (line near4 (wid$2 or edge) near4 rough$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
16	0	(((under or bottom or conductive or metal$4 or dielectric) near14 (deposit$4 or form$3 or layer or film or coat$3)) same pattern$4 same (substrate or wafer or device) same (pedestal or stage or hold$3)) and ((photoresist or resist or photo$4cur$4 or photo$3imageable) same (expos$4 or illuminat$4 or irradiat$4) same pattern$4) and develop$4 and (etch$4 or RIE or (dry near5 etch$4)) and (CD or (critical near5 dimension)) and ((LER or LWR or (line near4 (wid$2 or edge) near4 rough$5)) same (nm or nanometer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
17	0	(((under or bottom or conductive or metal$4 or dielectric) near14 (deposit$4 or form$3 or layer or film or coat$3)) same pattern$4 same (substrate or wafer or device) same (pedestal or stage or hold$3)) and ((photoresist or resist or photo$4cur$4 or photo$3imageable) same (expos$4 or illuminat$4 or irradiat$4) same pattern$4) and develop$4 and (etch$4 or RIE or (dry near5 etch$4)) and (CD or (critical near5 dimension)) and (LER or LWR or (line near4 (wid$2 or edge) near4 rough$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
18	2	(((under or bottom or conductive or metal$4 or dielectric) near14 (deposit$4 or form$3 or layer or film or coat$3)) same pattern$4) and ((photoresist or resist or photo$4cur$4 or photo$3imageable) same (substrate or wafer or device) same (pedestal or stage or hold$3) same (expos$4 or illuminat$4 or irradiat$4) same pattern$4) and develop$4 and (etch$4 or RIE or (dry near5 etch$4)) and (CD or (critical near5 dimension)) and (LER or LWR or (line near4 (wid$2 or edge) near4 rough$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
19	34	((under or bottom or conductive or metal$4 or dielectric) near14 (deposit$4 or form$3 or layer or film or coat$3)) and ((photoresist or resist or photo$4cur$4 or photo$3imageable) same (expos$4 or illuminat$4 or irradiat$4) same pattern$4) and develop$4 and (etch$4 or RIE or (dry near5 etch$4)) and ((CD or (critical near5 dimension)) same (nm or nanometer)) and ((LER or LWR or (line near4 (wid$2 or edge) near4 rough$5)) same (nm or nanometer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
20	19	(((under or bottom or conductive or metal$4 or dielectric) near14 (deposit$4 or form$3 or layer or film or coat$3)) same pattern$4) and ((photoresist or resist or photo$4cur$4 or photo$3imageable) same (novolac or epoxy or resin$3) same vinyl same (((photoactive or photo$4acid) near7 (generat$4 or liberat$4)) or PAG or (acid near8 (generat$4 or liberat$4))) same (expos$4 or illuminat$4 or irradiat$4) same pattern$4) and develop$4 and ((solubilization or $3solubilizing or soluble or solubility or insoluble) same (prevent$4 or caus$4 or inhibit$4)) and (etch$4 or RIE or (dry near5 etch$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
21	36	((bottom or conductive or metal$4 or dielectric or circuit$4) near14 (deposit$4 or form$3 or layer or film or coat$3)) and ((photoresist or resist or photo$4cur$4 or photo$3imageable) same (expos$4 or illuminat$4 or irradiat$4) same pattern$4) and develop$4 and ((CD or (critical near5 dimension)) same (nm or nanometer)) and ((LER or LWR or (line near4 (wid$2 or edge) near4 rough$5)) same (nm or nanometer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
22	15	((bottom or conductive or metal$4 or dielectric or circuit$4) near14 (deposit$4 or form$3 or layer or film or coat$3)) and (photolithograph$6) and develop$4 and ((CD or (critical near5 dimension)) same (nm or nanometer)) and ((LER or LWR or (line near4 (wid$2 or edge) near4 rough$5)) same (nm or nanometer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB